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MOS FET  
 MTM861280LBF

MTM861280LBF  
 Silicon P-channel MOSFET

For Switching

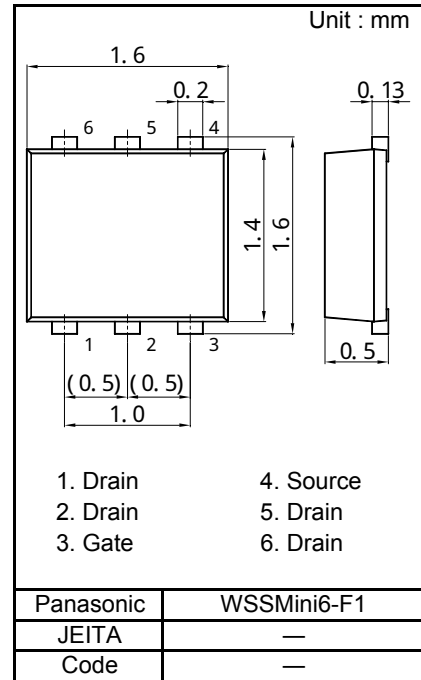
■ Features

- Low drain-source On-state Resistance  
 : RDS(on) typ. = 300 mΩ (VGS = -4.0 V)
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : ML

■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)



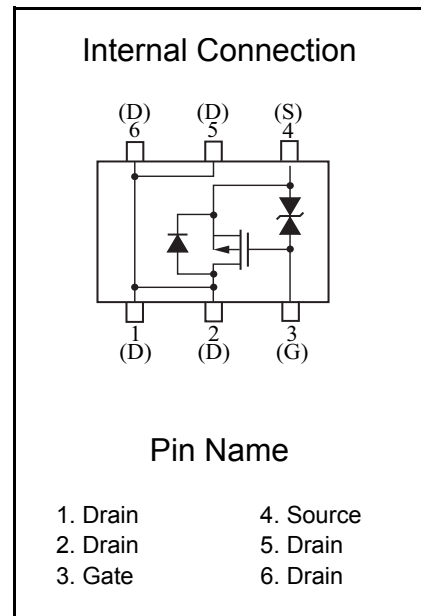
■ Absolute Maximum Ratings Ta = 25 °C

| Parameter                            | Symbol            | Rating      | Unit |
|--------------------------------------|-------------------|-------------|------|
| Drain to Source Voltage              | VDS               | -20         | V    |
| Gate to Source Voltage               | VGS               | ±12         |      |
| Drain Current                        | ID                | -1.0        |      |
| Drain Current (Pulsed) <sup>*1</sup> | IDp               | -4.0        | A    |
| Total Power Dissipation              | PD1 <sup>*2</sup> | 540         | mW   |
|                                      | PD2 <sup>*3</sup> | 150         |      |
| Channel Temperature                  | Tch               | 150         | °C   |
| Operating Ambient Temperature        | Topr              | -40 to +85  |      |
| Storage Temperature Range            | Tstg              | -55 to +150 |      |

Note) \*1 t ≤ 10 μs, Duty cycle ≤ 1 %

\*2 Glass epoxy substrate (25.4 × 25.4 × t 0.8 mm) coated with copper foil (more than 300 mm<sup>2</sup>)

\*3 Non-heat sink





■ Electrical Characteristics Ta = 25 °C ± 3 °C

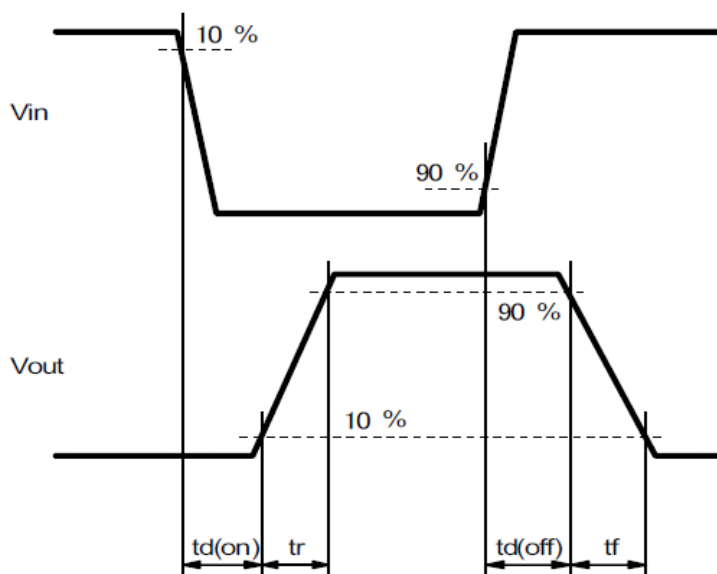
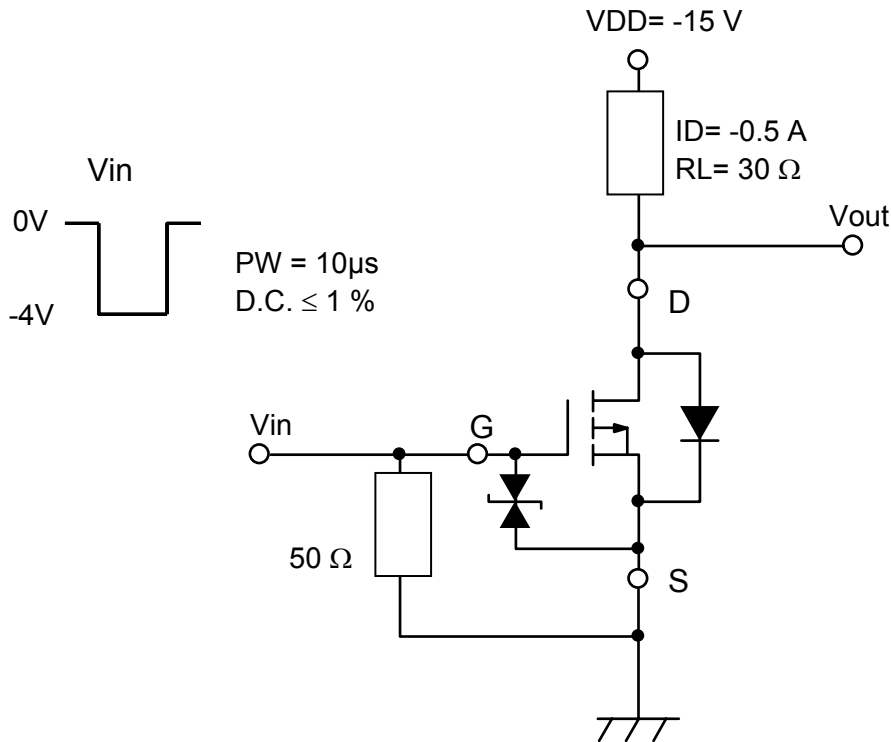
| Parameter                           | Symbol   | Conditions                          | Min   | Typ  | Max  | Unit |
|-------------------------------------|----------|-------------------------------------|-------|------|------|------|
| Drain-source Breakdown Voltage      | VDSS     | ID = -1.0 mA, VGS = 0 V             | -20   |      |      | V    |
| Zero Gate Voltage Drain Current     | IDSS     | VDS = -20 V, VGS = 0 V              |       |      | -1.0 | μA   |
| Gate-source Leakage Current         | IGSS     | VGS = ±10 V, VDS = 0 V              |       |      | ±10  | μA   |
| Gate-source Threshold Voltage       | Vth      | ID = -1.0 mA, VDS = -10 V           | -0.45 | -1.0 | -1.5 | V    |
| Drain-source On-state Resistance *1 | RDS(on)1 | ID = -0.5 A, VGS = -4.0 V           |       | 300  | 420  | mΩ   |
|                                     | RDS(on)2 | ID = -0.5 A, VGS = -2.5 V           |       | 420  | 560  |      |
| Forward transfer admittance *1      | Yfs      | ID = -0.5 A, VDS = -10 V            | 1.0   | 2.0  |      | S    |
| Input Capacitance                   | Ciss     | VDS = -10 V, VGS = 0 V<br>f = 1 MHz |       | 80   |      | pF   |
| Output Capacitance                  | Coss     |                                     |       | 12   |      |      |
| Reverse Transfer Capacitance        | Crss     |                                     |       | 12   |      |      |
| Turn-on Delay Time *2               | td(on)   | VDD = -15 V, VGS = 0 to -4 V        |       | 12   |      | ns   |
| Rise Time *2                        | tr       | ID = -0.5 A                         |       | 6    |      |      |
| Turn-off Delay Time *2              | td(off)  | VDD = -15 V, VGS = -4 to 0 V        |       | 17   |      | ns   |
| Fall Time *2                        | tf       | ID = -0.5 A                         |       | 10   |      |      |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

\*1 Pulse test

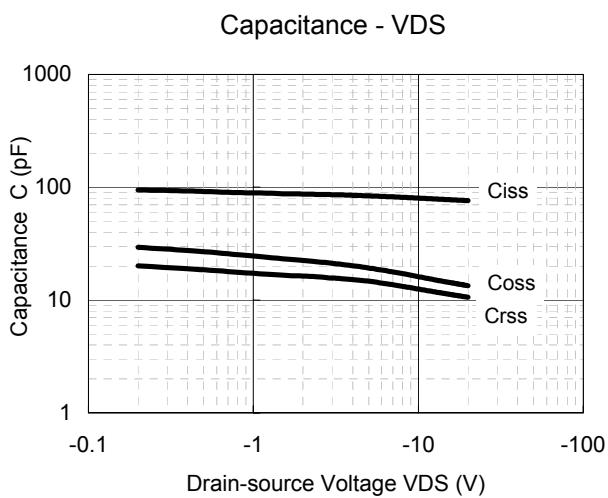
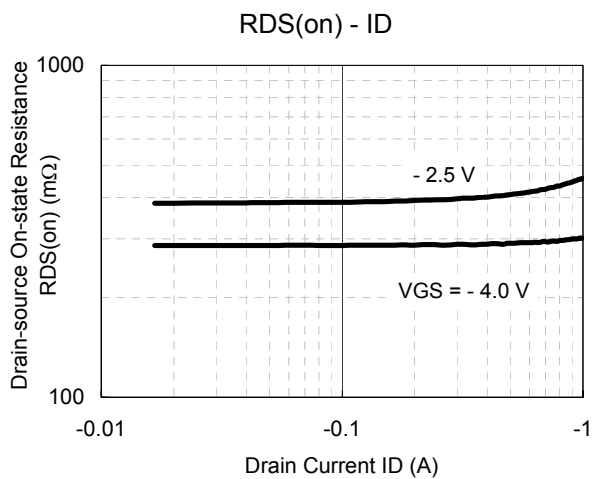
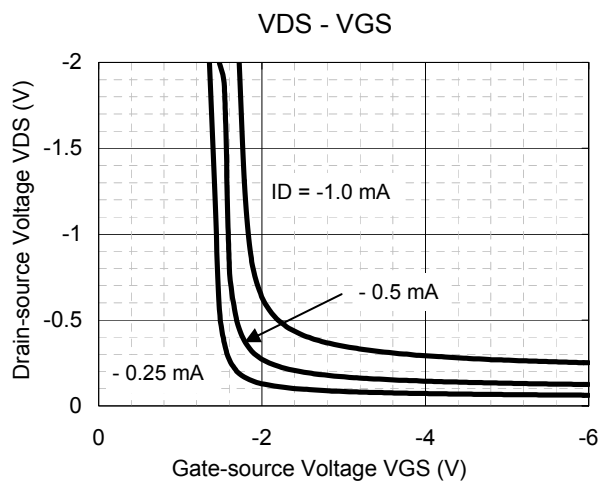
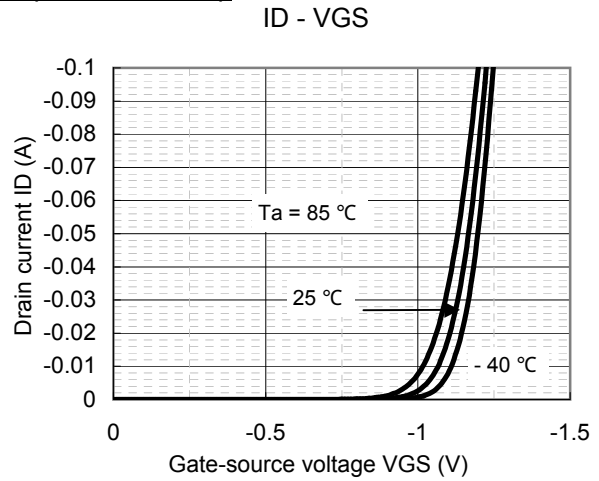
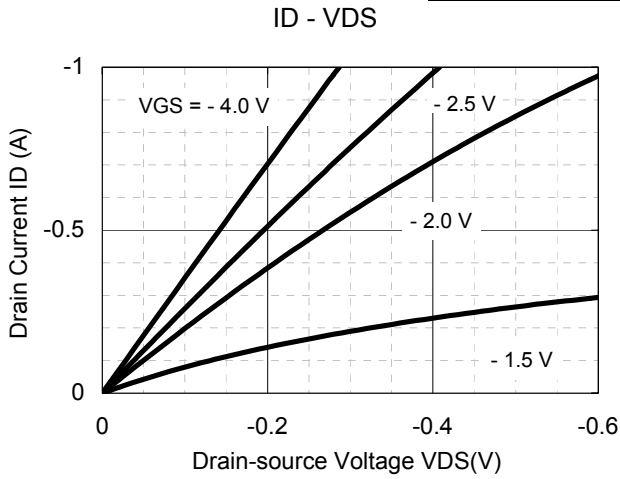
\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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Technical Data ( reference )

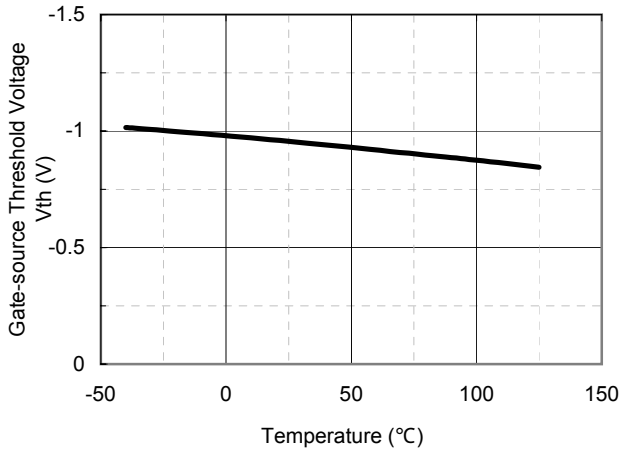




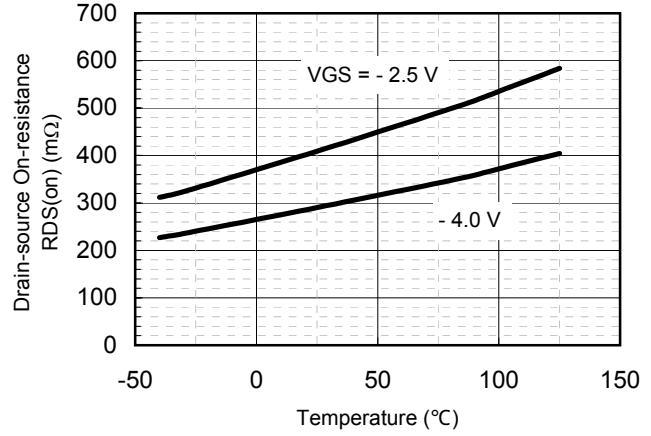


Technical Data ( reference )

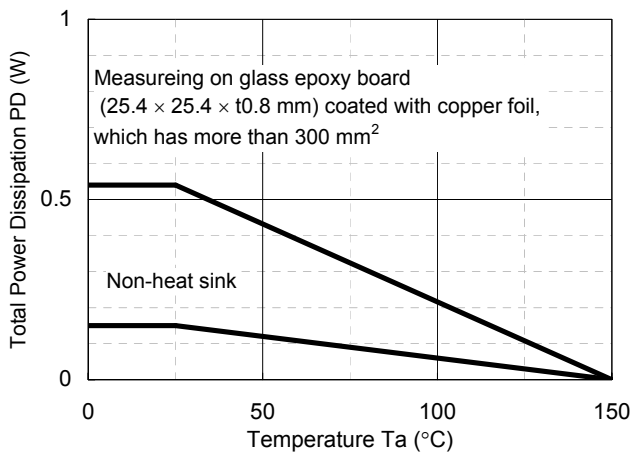
V<sub>th</sub> - T<sub>a</sub>



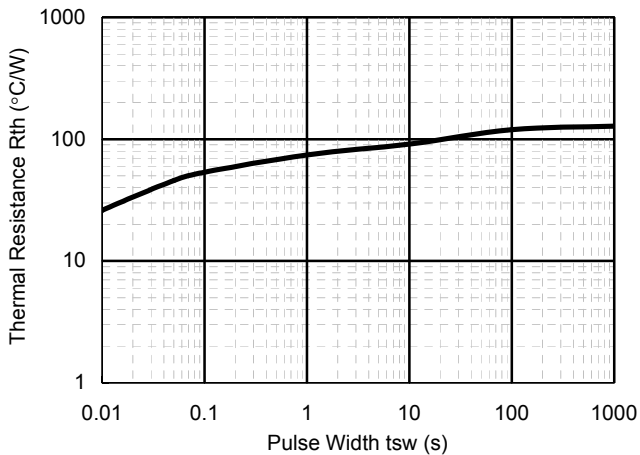
R<sub>DS(on)</sub> - T<sub>a</sub>



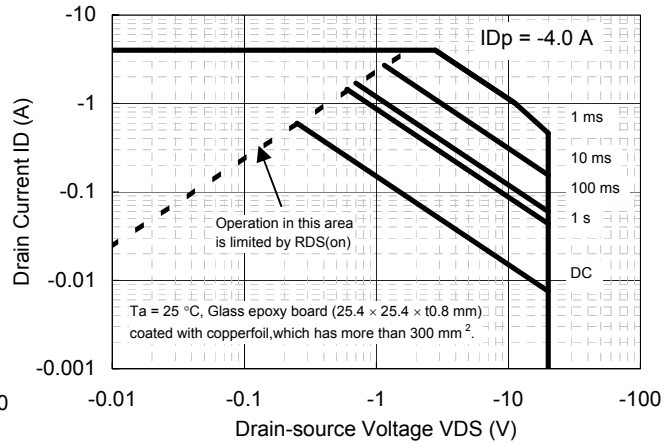
PD - T<sub>a</sub>



R<sub>th</sub> - t<sub>sw</sub>



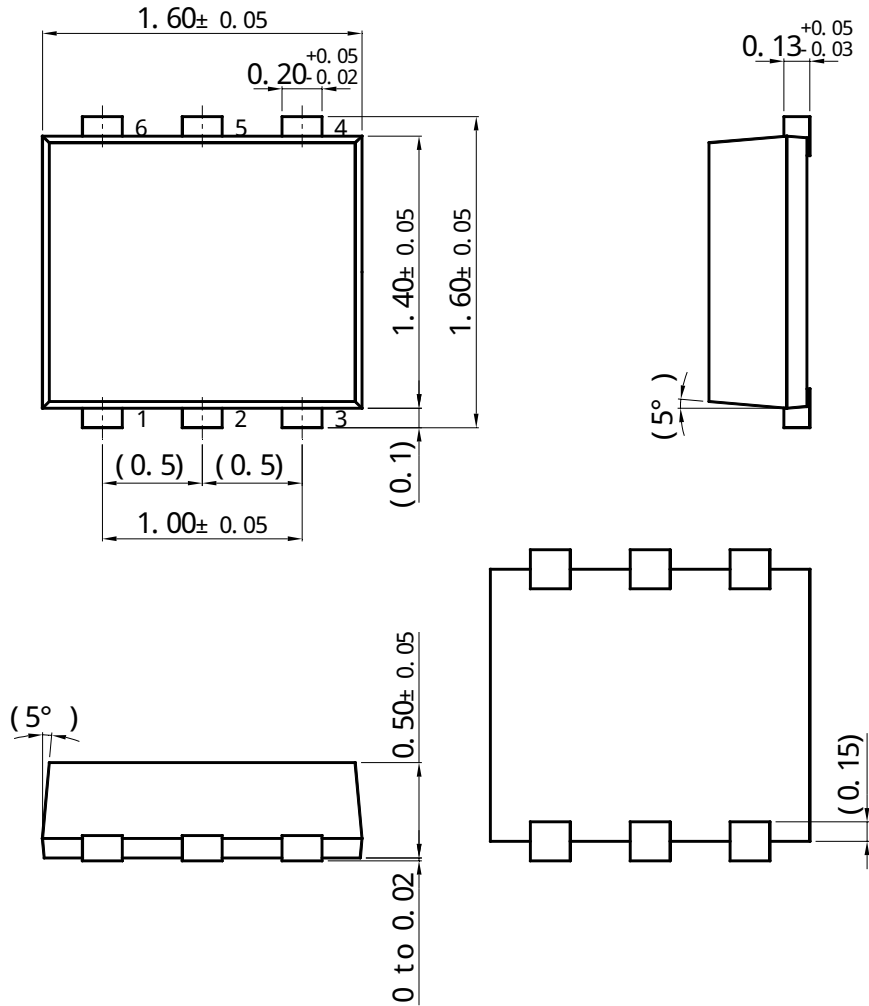
Safe Operating Area



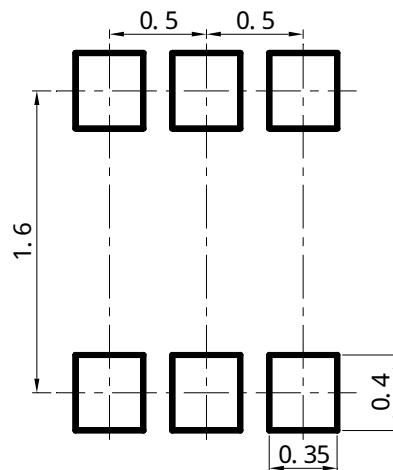


### WSSMini6-F1

Unit : mm



#### ■ Land Pattern (Reference) (Unit : mm)



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